



# PSMN1R0-30YLD

N-channel 30 V, 1.0 m $\Omega$  logic level MOSFET in LPAK56  
using NextPowerS3 Technology

19 September 2014

Product data sheet

## 1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LPAK56 package. NextPowerS3 portfolio utilising NXP's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Ultra low  $Q_G$ ,  $Q_{GD}$  and  $Q_{OSS}$  for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1  $\mu$ A leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

## 3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control
- Power OR-ing

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	25 °C $\leq T_J \leq$ 175 °C		-	-	30	V
$I_D$	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; <a href="#">Fig. 2</a>	[1]	-	-	100	A
$P_{tot}$	total power dissipation	$T_{mb} = 25$ °C; <a href="#">Fig. 1</a>		-	-	238	W



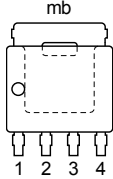
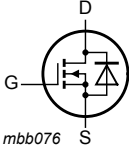
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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	1	1.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>		-	0.79	1.02	mΩ
Dynamic characteristics							
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	10.9	16.35	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>		-	38.2	57.3	nC
Source-drain diode							
S	softness factor	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; dI <sub>S</sub> /dt = -100 A/μs; V <sub>DS</sub> = 15 V; <a href="#">Fig. 16</a>		-	0.95	-	

[1] Continuous current is limited by package.

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LFAK56; Power-SO8 (SOT669)</b></p>	 <p><i>mbb076</i></p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R0-30YLD	LFAK56; Power-SO8	Plastic single-ended surface-mounted package (LFAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R0-30YLD	1D030L

## 8. Limiting values

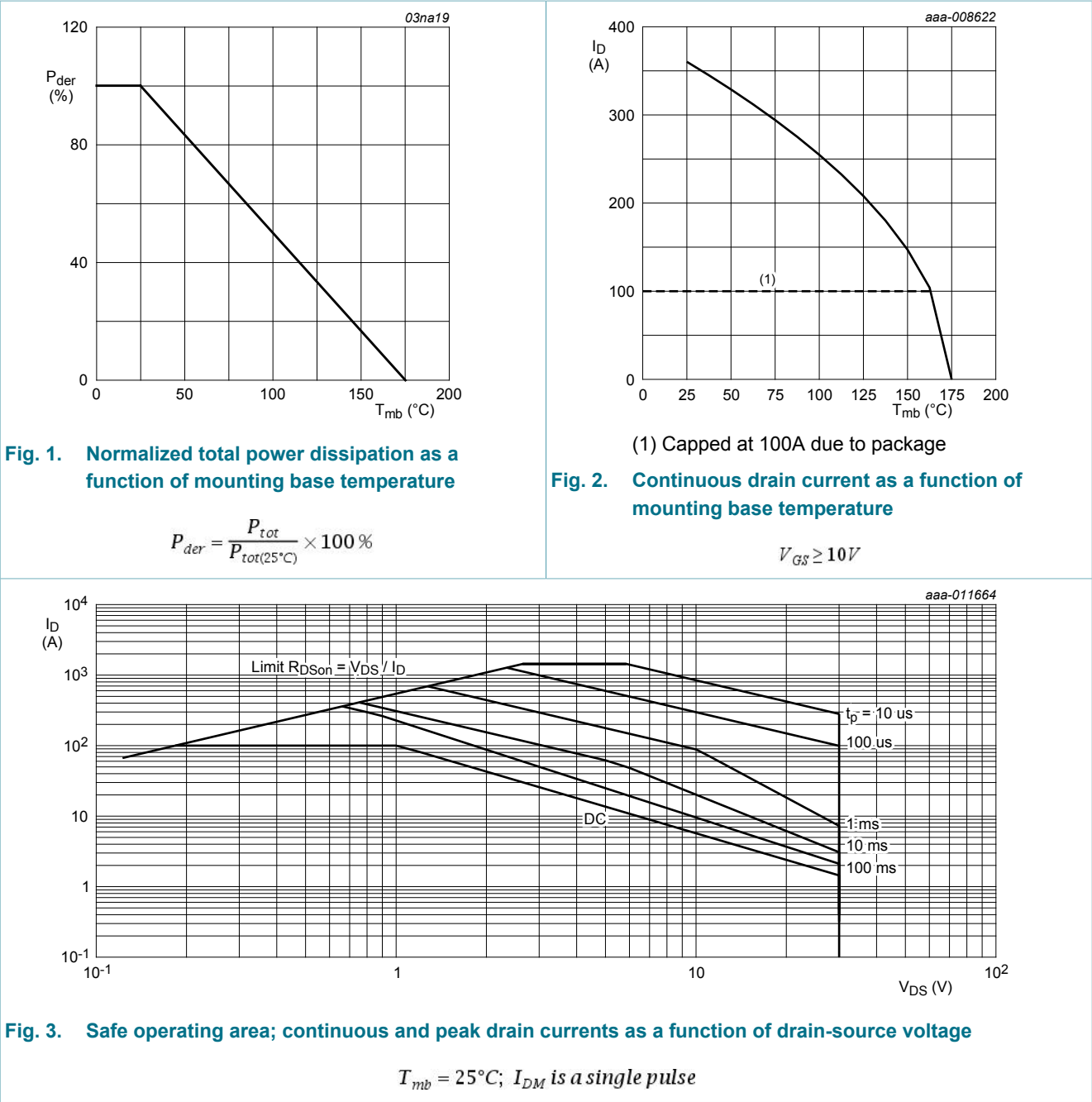
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_J \leq 175\text{ °C}$		-	30	V
$V_{DGR}$	drain-gate voltage	$25\text{ °C} \leq T_J \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>		-	238	W
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	<a href="#">[1]</a>	-	100	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>	<a href="#">[1]</a>	-	100	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>		-	1441	A
$T_{stg}$	storage temperature			-55	175	°C
$T_J$	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
$V_{ESD}$	electrostatic discharge voltage	HBM		1500	-	V
<b>Source-drain diode</b>						
$I_S$	source current	$T_{mb} = 25\text{ °C}$	<a href="#">[1]</a>	-	100	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$		-	1441	A
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{J(\text{init})} = 25\text{ °C}$ ; $I_D = 25\text{ A}$ ; $V_{sup} \leq 30\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; unclamped; $t_p = 3.3\text{ ms}$	<a href="#">[2]</a>	-	1588	mJ

[1] Continuous current is limited by package.

[2] Protected by 100% test



9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4		-	0.56	0.63	K/W

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W
		Fig. 6	-	125	-	K/W

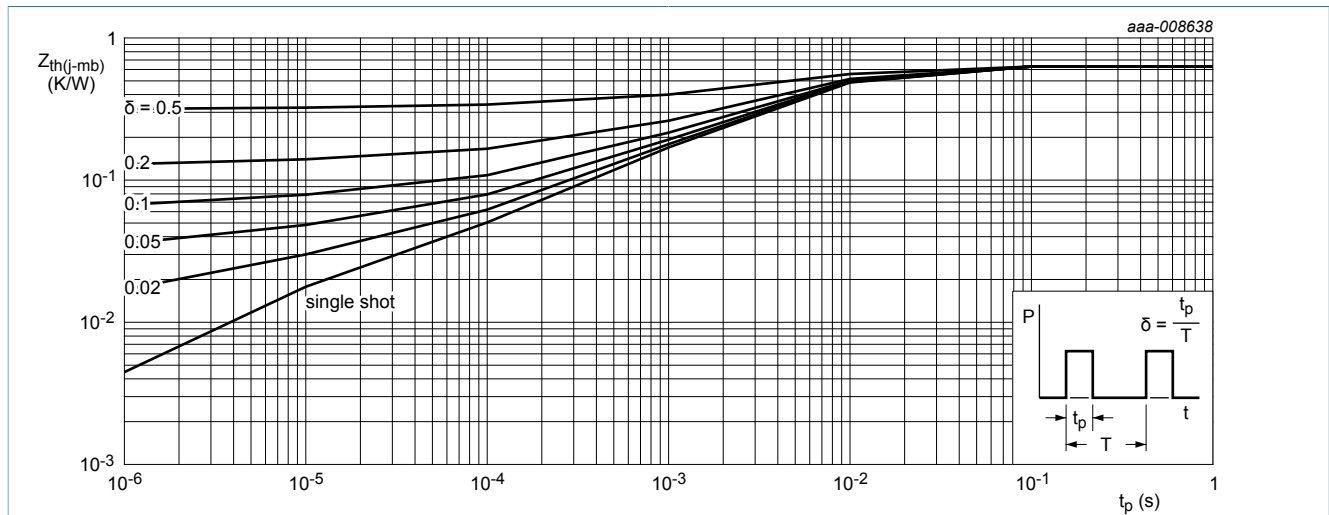


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

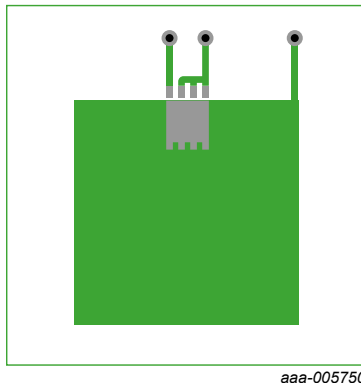


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

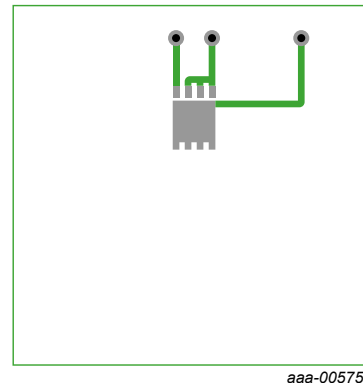


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 ^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 ^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 2 mA; V_{DS} = V_{GS}; T_J = 25 ^\circ C$	1.2	1.75	2.2	V

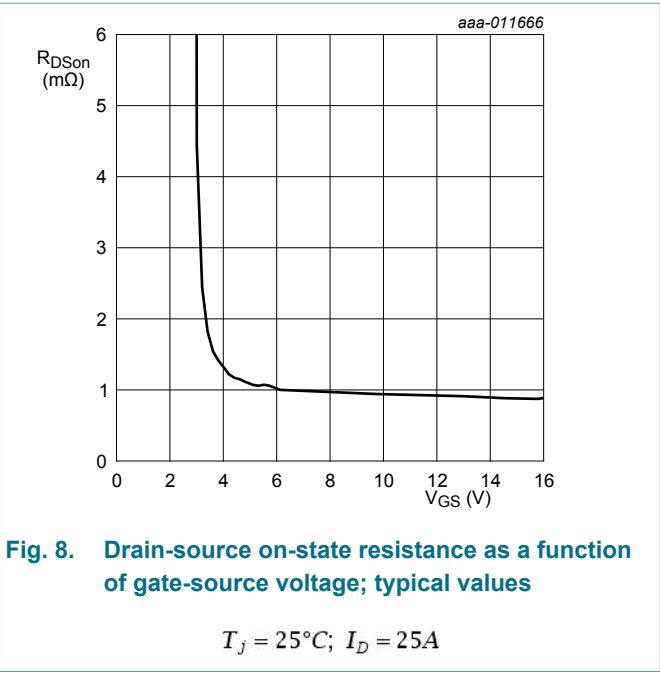
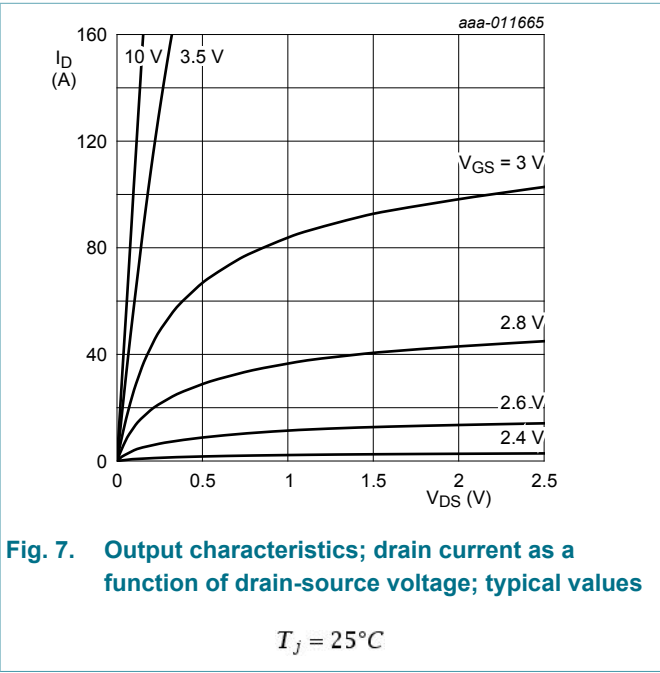
## N-channel 30 V, 1.0 mΩ logic level MOSFET in LPAK56 using NextPowerS3 Technology

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25\text{ }^{\circ}\text{C} \leq T_j \leq 150\text{ }^{\circ}\text{C}$	-	-4.9	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 24\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 24\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$	-	2.8	-	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{GS} = -16\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 10</a>	-	1	1.3	mΩ
		$V_{GS} = 4.5\text{ V}; I_D = 25\text{ A}; T_j = 150\text{ }^{\circ}\text{C};$ <a href="#">Fig. 11; Fig. 10</a>	-	-	2.15	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 10</a>	-	0.79	1.02	mΩ
		$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 150\text{ }^{\circ}\text{C};$ <a href="#">Fig. 11; Fig. 10</a>	-	-	1.7	mΩ
$R_G$	gate resistance	$f = 1\text{ MHz}$	-	1.22	2.44	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 10\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	80.9	121.35	nC
		$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	38.2	57.3	nC
		$I_D = 0\text{ A}; V_{DS} = 0\text{ V}; V_{GS} = 10\text{ V}$	-	72	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25\text{ A}; V_{DS} = 15\text{ V}; V_{GS} = 4.5\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	12.5	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	7.8	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	4.7	-	nC
$Q_{GD}$	gate-drain charge		-	10.9	16.35	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\text{ A}; V_{DS} = 15\text{ V};$ <a href="#">Fig. 12; Fig. 13</a>	-	2.6	-	V
$C_{iss}$	input capacitance	$V_{DS} = 15\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^{\circ}\text{C};$ <a href="#">Fig. 14</a>	-	5732	8598	pF
$C_{oss}$	output capacitance		-	2424	3636	pF
$C_{rss}$	reverse transfer capacitance		-	340	510	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 1\text{ }^{\circ}\Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 5\text{ }^{\circ}\Omega$	-	32.4	-	ns
$t_r$	rise time		-	44.4	-	ns
$t_{d(off)}$	turn-off delay time		-	43	-	ns
$t_f$	fall time		-	31.7	-	ns

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 15\text{ V}$ ; $f = 1\text{ MHz}$ ; $T_j = 25\text{ }^{\circ}\text{C}$		-	55.9	-	nC
Source-drain diode							
$V_{SD}$	source-drain voltage	$I_S = 25\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 15</a>		-	0.77	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 15\text{ V}$ ; <a href="#">Fig. 16</a>		-	51.8	103.6	ns
$Q_r$	recovered charge		<a href="#">[1]</a>	-	67.1	134.2	nC
$t_a$	reverse recovery rise time			-	26.5	-	ns
$t_b$	reverse recovery fall time			-	25.3	-	ns
S	softness factor			-	0.95	-	

[1] includes capacitive recovery



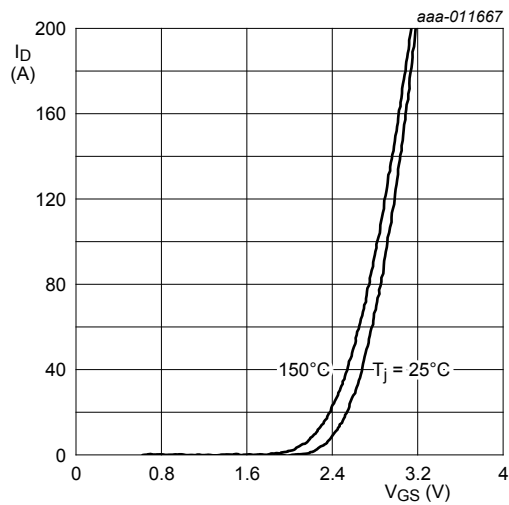


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 12V$$

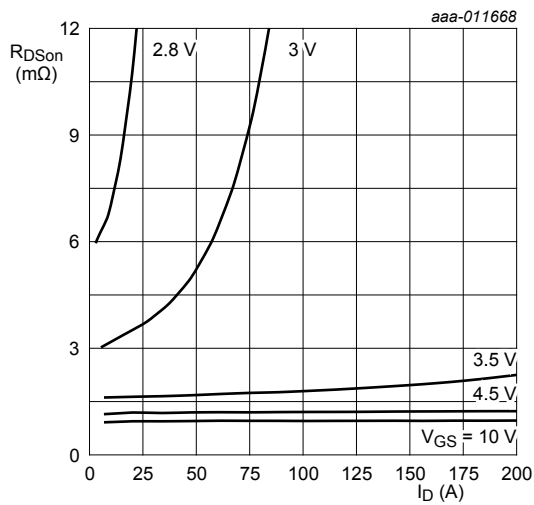


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

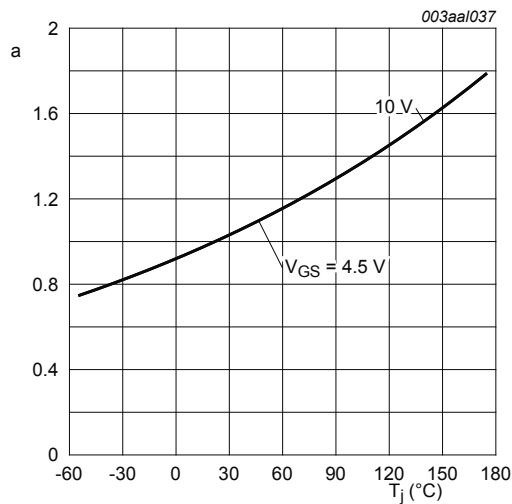


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

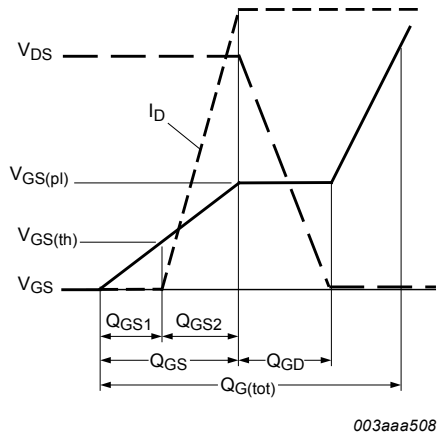


Fig. 12. Gate charge waveform definitions



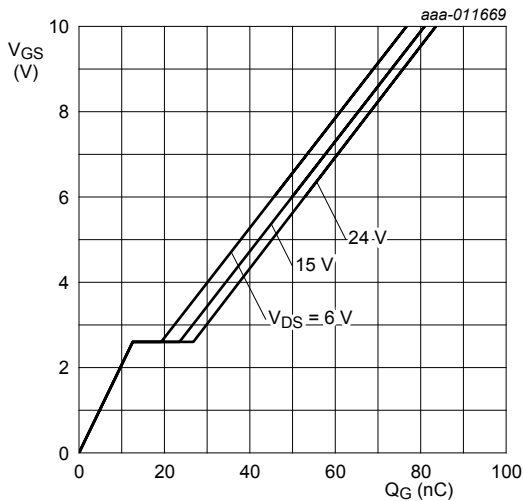


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^{\circ}\text{C}; I_D = 25\text{A}$

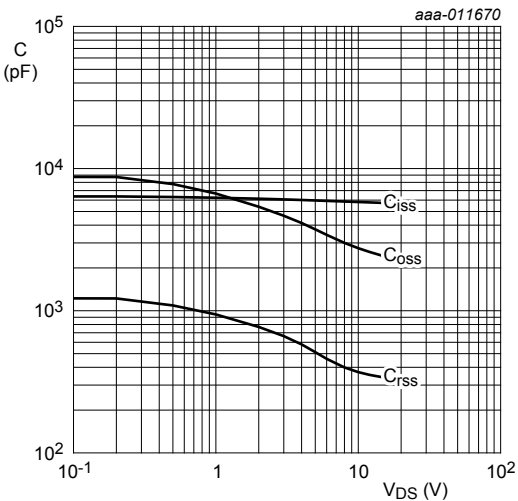


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{V}; f = 1\text{MHz}$

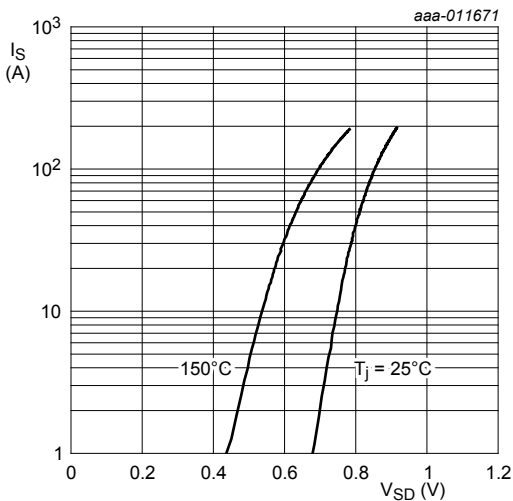


Fig. 15. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{V}$

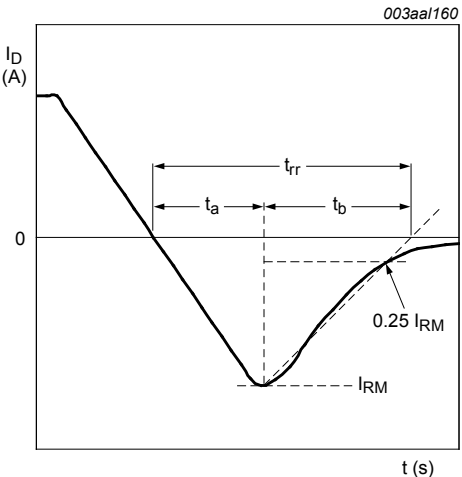


Fig. 16. Reverse recovery timing definition

11. Package outline

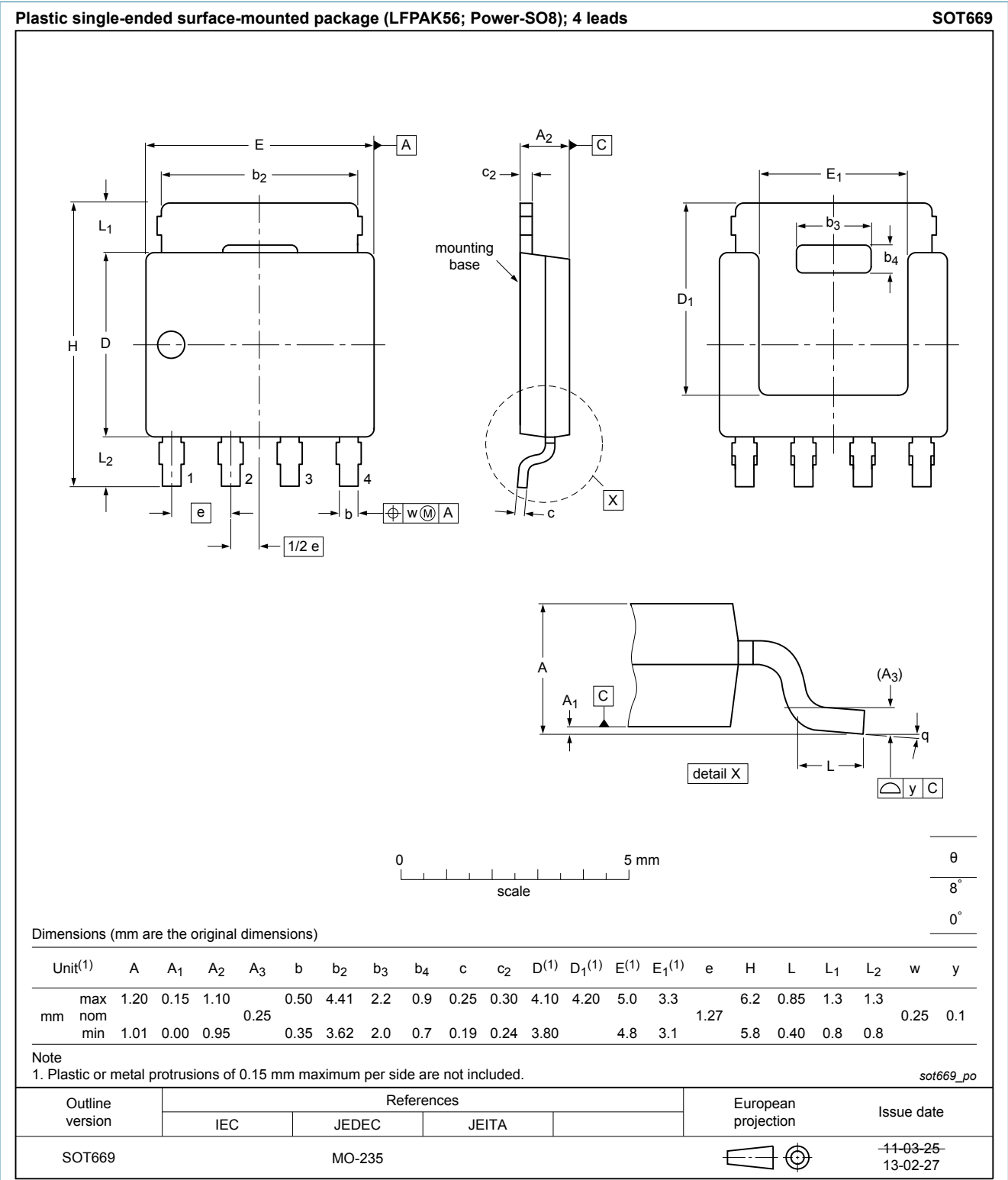


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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